Thyristor Surface Mount Phase Control SCR, 16 A



PRIMARY CHARACTERISTICS						
I _{T(AV)} 10 A						
V _{DRM} /V _{RRM}	1600 V					
V _{TM}	1.4 V					
I _{GT}	60 mA					
TJ	-40 °C to +125 °C					
Package	D ² PAK (TO-263AB)					
Circuit configuration	Single SCR					

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified according JEDEC[®]-JESD 47

RoHS COMPLIANT HALOGEN FREE

 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are in identical package outlines

DESCRIPTION

The VS-16TTS16S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS							
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 $\mu\text{m})$ copper	2.5	3.5					
Aluminum IMS, R _{thCA} = 15 °C/W	6.3	9.5	А				
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	14.0	18.5					

Note

• $T_A = 55 \text{ °C}, T_J = 125 \text{ °C}, \text{ footprint } 300 \text{ mm}^2$

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	10				
I _{RMS}		16	A			
V _{RRM} /V _{DRM}		1600	V			
I _{TSM}		200	A			
V _T	10 A, T _J = 25 °C	1.4	V			
dV/dt		500	V/µs			
dl/dt		150	A/µs			
TJ		-40 to +125	°C			

VOLTAGE RATINGS			
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} ∕I _{DRM} AT 125 °C mA
VS-16TTS16S-M3	1600	1600	10

 Revision: 04-Jan-18
 1
 Document Number: 96413

 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
 DiodesEurope@vishay.com

 THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000





VS-16TTS16S-M3 Series



Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL		TEST CONDITIONS	VAL	UNITS				
FARAMEIER	STWIDOL		TEST CONDITIONS	TYP.	MAX.				
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 18	0° conduction, half sine wave	1	0				
Maximum RMS on-state current	I _{RMS}			1	6	А			
Maximum peak, one-cycle,	I	10 ms sine pul	se, rated V _{RRM} applied	17	70	~			
non-repetitive surge current	I _{TSM}	10 ms sine pul	se, no voltage reapplied	20	00				
Maximum I ² t for fusing	l ² t	10 ms sine pul	se, rated V _{RRM} applied	144		A ² s			
Maximum Frontusing	10 ms sine pulse, no voltage r		se, no voltage reapplied	ied 200		~~5			
Maximum I²√t for fusing	l²√t	t = 0.1 ms to 1	t = 0.1 ms to 10 ms, no voltage reapplied			A²√s			
Maximum on-state voltage drop	V _{TM}	10 A, T _J = 25 °C		1.4		V			
On-state slope resistance	r _t	T _{.1} = 125 °C		24.0		mΩ			
Threshold voltage	V _{T(TO)}	1.1		.1	V				
Maximum reverse and direct leakage current	1	T _J = 25 °C	$T_{\rm J} = 25 ^{\circ}{\rm C}$ $V_{\rm R} = rated V_{\rm RRM} / V_{\rm DRM}$		0.5				
Maximum reverse and direct leakage current	'RM' 'DM	I_{RM}/I_{DM} $T_J = 125 \text{ °C}$		1	0				
Holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 $^\circ C$		100	150	mA			
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$			I_L Anode supply = 6 V, resistive load, $T_J = 2$		200		
Maximum rate of rise of off-state voltage	dV/dt	T _J = T _J max. li	near to 80 % $V_{DRM} = R_g - k = open$	= open 500		V/µs			
Maximum rate of rise of turned-on current	dl/dt			150		A/µs			

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak gate power	P _{GM}		8.0	W		
Maximum average gate power	P _{G(AV)}		2.0	vv		
Maximum peak positive gate current	+ I _{GM}		1.5	А		
Maximum peak negative gate voltage	- V _{GM}		10	V		
		Anode supply = 6 V, resistive load, T_J = - 10 °C	90	mA		
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T_J = 25 °C	60			
		Anode supply = 6 V, resistive load, T_J = 125 °C	35			
		Anode supply = 6 V, resistive load, T_J = - 10 °C	3.0			
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$				
Voltage to trigger		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	V		
Maximum DC gate voltage not to trigger	V_{GD}	T 105 °C V reteducius	0.25			
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = rated value	2.0	mA		

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9			
Typical reverse recovery time	t _{rr}	T₁ = 125 °C	4	μs		
Typical turn-off time	tq	1j = 125 C	110			

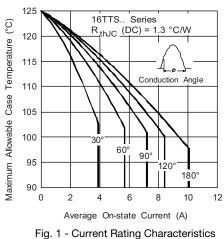


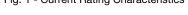
THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.3	°C/W		
Typical thermal resistance, junction to ambient	R _{thJA}	PCB mount ⁽¹⁾	40	0/10		
Approximate weight			2	g		
			0.07	oz.		
Marking device		Case style D ² PAK (TO-263AB)	16TTS	16S		

Note

 $^{(1)}$ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W.

For recommended footprint and soldering techniques refer to application note #AN-994





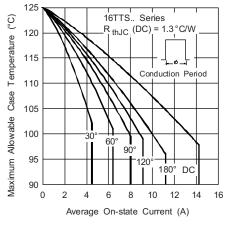


Fig. 2 - Current Rating Characteristics

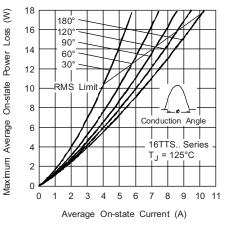


Fig. 3 - On-State Power Loss Characteristics

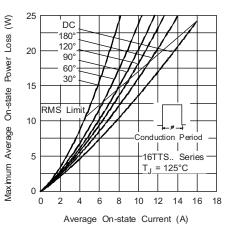


Fig. 4 - On-State Power Loss Characteristics

Revision: 04-Jan-18	
E au ta alemia al	

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



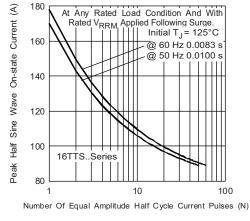
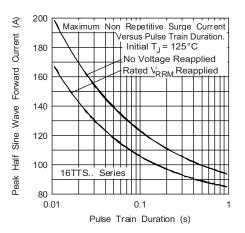
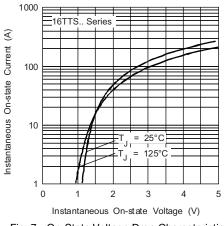


Fig. 5 - Maximum Non-Repetitive Surge Current









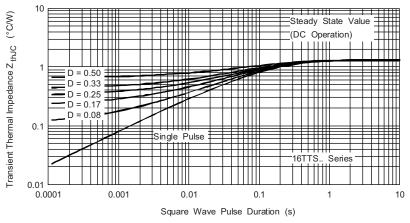
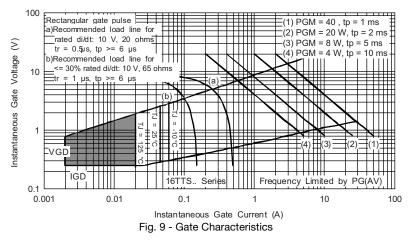


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

VS-16TTS16S-M3 Series

Vishay Semiconductors



ORDERING INFORMATION TABLE

www.vishay.com

Device code	VS-	16	т	т	s	16	S	TRL	-M3
		2	3	4	5	6	7	8	9
	1 -	Visl	nay Sen	niconduc	ctors pro	oduct			
	2 -	- Cur	rent rati	ng					
	3 -	· Circ	cuit conf	iguratio	า:				
		T =	single t	hyristor					
	4 -	· Pac	kage:						
		T =	D ² PAK	(TO-26	3AB)				
	5 -	. Тур	e of silio	con:					
		S =	standa	rd recov	ery rect	ifier			
	6 -	· Vol	tage rati	ng: Volt	age cod	le x 100	= V _{RRI}	_N (16 = ⁻	1600 V)
	7 -	- S =	surface	mounta	able				
	8 -	• No	one = tu	be					
		• TF	RL = tap	e and re	el (left o	oriented)		
		• TF	RR = tap	be and r	eel (righ	it oriente	ed)		
	9	-M3	8 = halog	gen-free	, RoHS-	-complia	ant, and	l termina	ations le

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-16TTS16S-M3	50	1000	Antistatic plastic tubes				
VS-16TTS16STRR-M3	800	800	13" diameter reel				
VS-16TTS16STRL-M3	800	800	13" diameter reel				

LINKS TO RELATED DOCUMENTS					
Dimensions	<u>w</u>	ww.vishay.com/doc?96164			
Part marking information www.vishay.com/doc?95444					
Packaging information	W	ww.vishay.com/doc?96424			
Revision: 04-Jan-18	5	Document Number: 96413			
For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com					

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

D²PAK

DIMENSIONS in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIMETERS		INCHES		NOTES	
	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIMETERS		INCHES		NOTES	
	STNDUL	MIN.	MAX.	MIN.	MAX.	NOTES
	D1	6.86	8.00	0.270	0.315	3
	E	9.65	10.67	0.380	0.420	2, 3
	E1	7.90	8.80	0.311	0.346	3
	е	2.54 BSC		0.100 BSC		
	Н	14.61	15.88	0.575	0.625	
	L	1.78	2.79	0.070	0.110	
	L1	-	1.65	-	0.066	3
	L2	1.27	1.78	0.050	0.070	
	L3	0.25 BSC		0.010 BSC		
	L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 13-Jul-17

1

Document Number: 96164

For technical questions within your region: DiodesAmericas@vishav.com, DiodesAsia@vishav.com, DiodesEurope@vishav.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishav.com/doc?91000





Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.